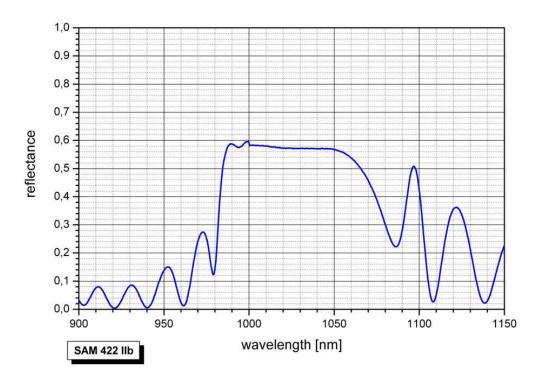


SAMTM Data Sheet SAM-1040-40-9ps-x, λ = 1040 nm

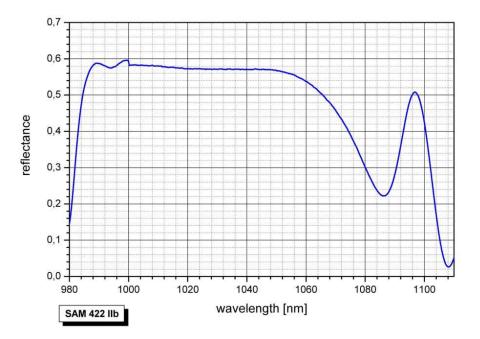
Laser wavelength	$\lambda = 1040 \text{ nm}$
High reflection band	λ = 990 1064 nm
Absorptance	$A_0 = 40 \%$
Modulation depth	∆R = 29 %
Non-saturable loss	A _{ns} = 11 %
Saturation fluence	Φ_{sat} = 90 µJ/cm ²
Relaxation time constant	τ ~ 9 ps
Damage threshold	$\Phi = 1 \text{ mJ/cm}^2$
Chip area	4.0 mm x 4.0 mm; other dimensions on request
Chip thickness	450 μm
Protection	the SAM is protected with a dielectric front layer
Mounting option x denotes the type of mounting as follows: $\mathbf{x} = 0$ unmounted	
x = 12.7 g	glued on a gold plated Cu-cylinder with 12.7 mm $arnothing$

x = 12.7 g	glued on a gold plated Cu-cylinder with 12.7 mm \oslash
x = 25.4 g	glued on a gold plated Cu-cylinder with 25.4 mm $arnothing$
x = 12.7 s	soldered on a gold plated Cu-cylinder with 12.7 mm $arnothing$
x = 25.4 s	soldered on a gold plated Cu-cylinder with 25.4 mm $arnothing$
x = FC	mounted on a 1 m monomode fiber cable with FC connector

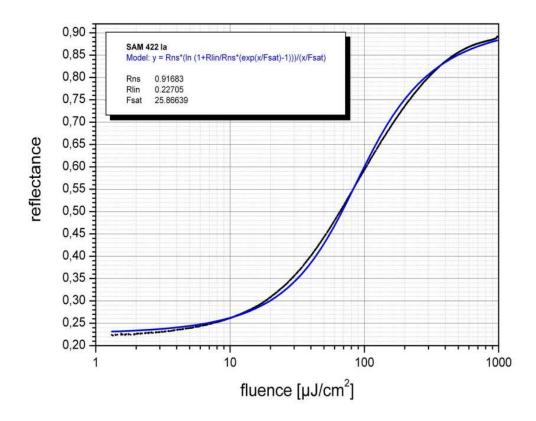
Low intensity spectral reflectance







Saturation measurement of a SAM-1040-80 from the same wafer



Relaxation of a SAM-1040-80 from the same wafer, pump-probe measurement



